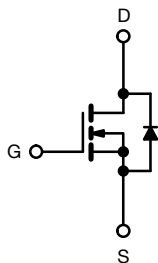
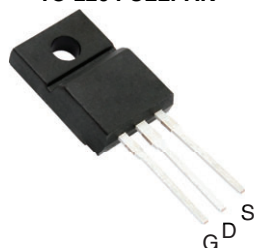


Power MOSFET

TO-220 FULLPAK


N-Channel MOSFET

FEATURES

- Isolated package
- High voltage isolation = 2.5 kV_{RMS} (t = 60 s; f = 60 Hz)
- Sink to lead creepage distance = 4.8 mm
- Dynamic dV/dt rating
- Low thermal resistance
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 FULLPAK eliminates the need for additional insulating hardware in commercial-industrial applications. The molding compound used provides a high isolation capability and a low thermal resistance between the tab and external heatsink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The FULLPAK is mounted to a heatsink using a single clip or by a single screw fixing.

PRODUCT SUMMARY

V _{DS} (V)	250	
R _{DS(on)} (Ω)	V _{GS} = 10 V	0.45
Q _g max. (nC)	41	
Q _{gs} (nC)	6.5	
Q _{gd} (nC)	22	
Configuration	Single	

ORDERING INFORMATION

Package	TO-220 FULLPAK
Lead (Pb)-free	IRFI634GPbF

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER				SYMBOL	LIMIT	UNIT
Drain-source voltage				V _{DS}	250	V
Gate-source voltage				V _{GS}	± 20	
Continuous drain current	V _{GS} at 10 V	T _C = 25 °C	I _D	5.6	A	
		T _C = 100 °C		3.5		
Pulsed drain current ^a				I _{DM}	22	
Linear derating factor					0.28	W/°C
Single pulse avalanche energy ^b				E _{AS}	300	mJ
Repetitive avalanche current ^a				I _{AR}	5.6	A
Repetitive avalanche energy ^a				E _{AR}	3.5	mJ
Maximum power dissipation		T _C = 25 °C		P _D	35	W
Peak diode recovery dV/dt ^c				dV/dt	4.8	V/ns
Operating junction and storage temperature range				T _J , T _{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) ^d		For 10 s			300	
Mounting torque		M3 screw			0.6	Nm

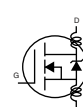
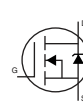
Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- V_{DD} = 50 V, starting T_J = 25 °C, L = 15 mH, R_g = 25 Ω, I_{AS} = 5.6 A (see fig. 12)
- I_{SD} ≤ 5.6 A, dI/dt ≤ 120 A/μs, V_{DD} ≤ V_{DS}, T_J ≤ 150 °C
- 1.6 mm from case

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	65	°C/W
Maximum junction-to-case (drain)	R_{thJC}	-	3.6	

SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-ssource breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		250	-	-	V
V _{DS} temperature coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA		-	0.30	-	V/°C
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.0	-	4.0	V
Gate-source leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 250 V, V _{GS} = 0 V		-	-	25	μA
		V _{DS} = 200 V, V _{GS} = 0 V, T _J = 125 °C		-	-	250	
Drain-source on-state resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 3.4 A ^b	-	-	0.45	Ω
Forward transconductance	g _{fs}	V _{DS} = 50 V, I _D = 3.4 A ^b		2.5	-	-	S
Dynamic							
Input capacitance	C _{iSS}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1.0 MHz, see fig. 5		-	770	-	pF
Output capacitance	C _{OSS}			-	190	-	
Reverse transfer capacitance	C _{rSS}			-	52	-	
Drain to sink capacitance	C	f = 1.0 MHz		-	12	-	
Total gate charge	Q _g	V _{GS} = 10 V	I _D = 5.6 A, V _{DS} = 200 V, see fig. 6 and 13 ^b	-	-	41	nC
Gate-source charge	Q _{gs}			-	-	6.5	
Gate-drain charge	Q _{gd}			-	-	22	
Turn-on delay time	t _{d(on)}	V _{DD} = 125 V, I _D = 5.6 A, R _g = 12 Ω, R _D = 22 Ω, see fig. 10 ^b		-	9.6	-	ns
Rise time	t _r			-	21	-	
Turn-off delay time	t _{d(off)}			-	42	-	
Fall time	t _f			-	19	-	
Gate input resistance	R _g	f = 1 MHz, open drain		0.5	-	2.4	Ω
Internal drain inductance	L _D	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	nH
Internal source inductance	L _S			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	5.6	A
Pulsed diode forward current ^a	I _{SM}			-	-	22	
Body diode voltage	V _{SD}	T _J = 25 °C, I _S = 5.6 A, V _{GS} = 0 V ^b		-	-	2.0	V
Body diode reverse recovery time	t _{rr}	T _J = 25 °C, I _F = 5.6 A, dI/dt = 100 A/μs ^b		-	220	440	ns
Body diode reverse recovery charge	Q _{rr}			-	1.2	2.4	μC
Forward turn-on time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D)					

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\text{ }\%$

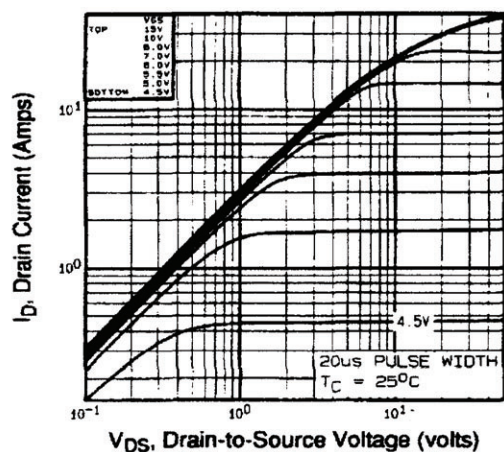
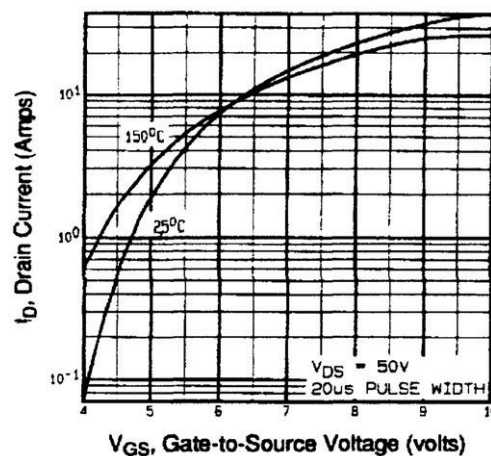
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^{\circ}\text{C}$


Fig. 3 - Typical Transfer Characteristics

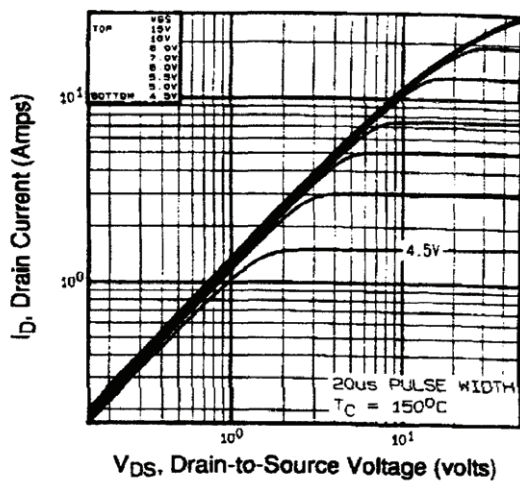
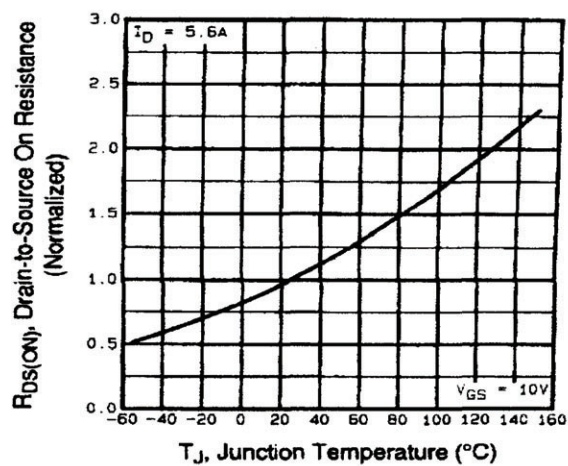

Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ }^{\circ}\text{C}$


Fig. 4 - Normalized On-Resistance vs. Temperature

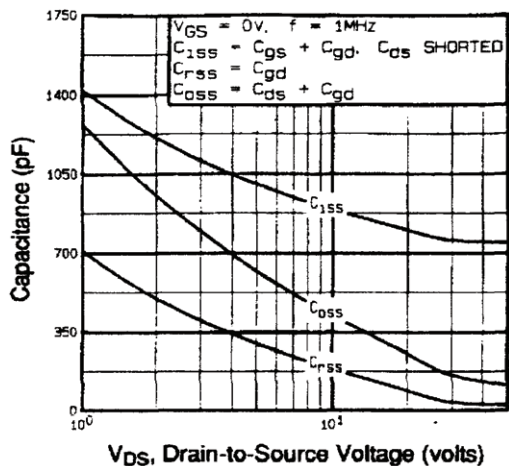


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

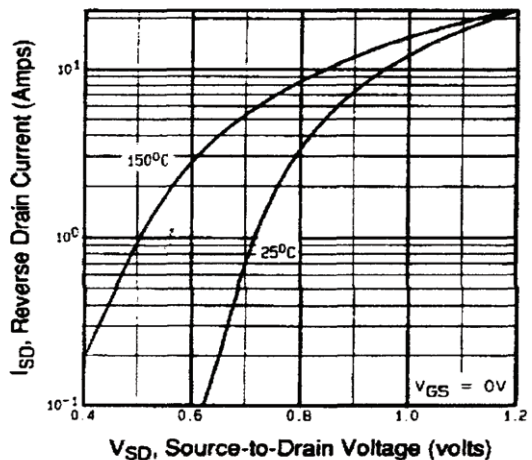


Fig. 7 - Typical Source-Drain Diode Forward Voltage

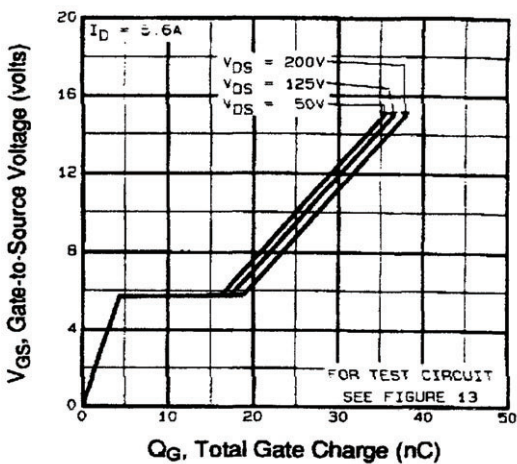


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

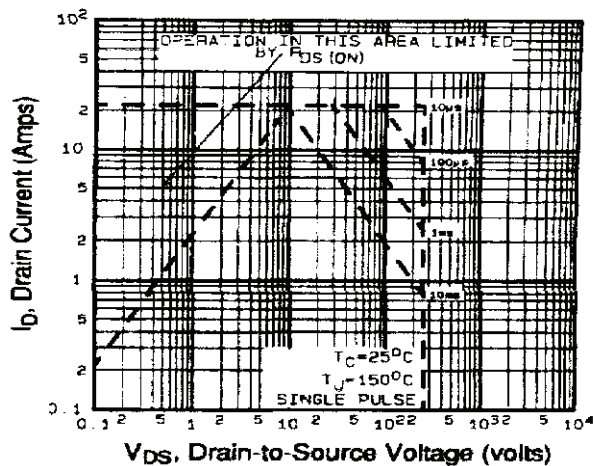
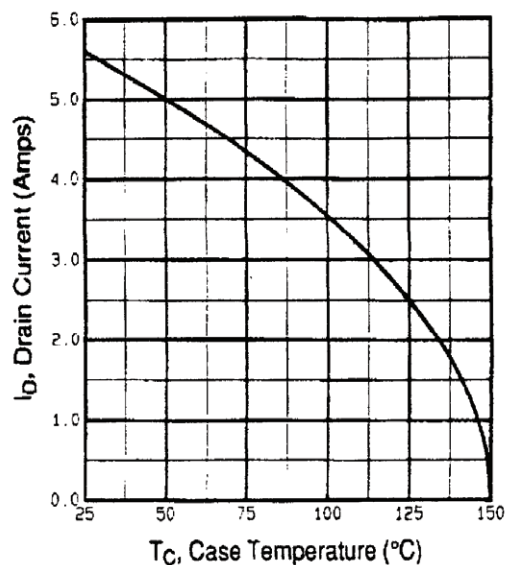
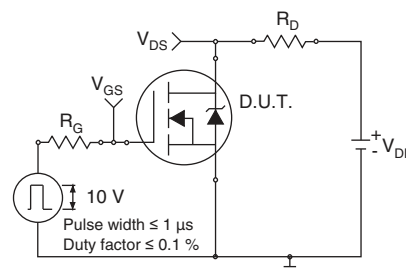
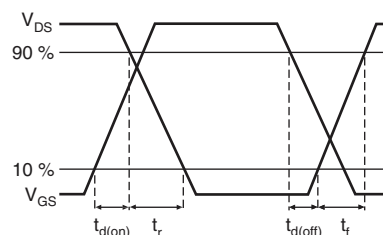
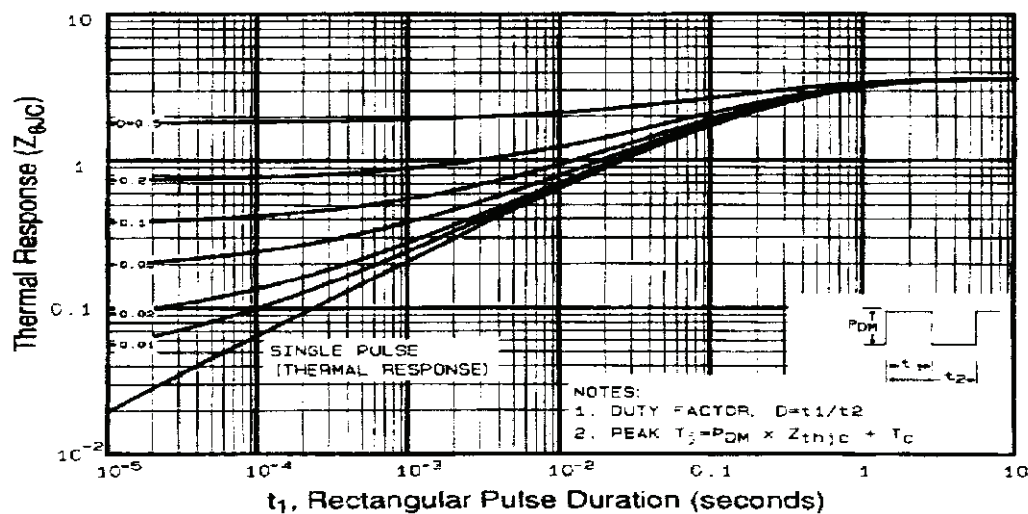
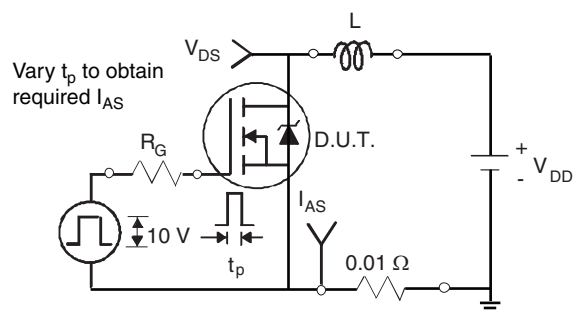
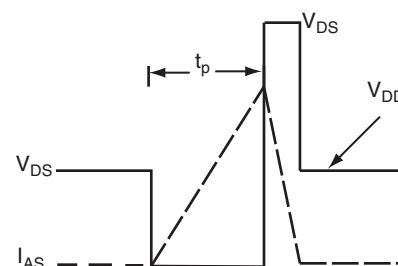


Fig. 8 - Maximum Safe Operating Area


Fig. 9 - Maximum Drain Current vs. Case Temperature

Fig. 10a - Switching Time Test Circuit

Fig. 10b - Switching Time Waveforms

Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

Fig. 12a - Unclamped Inductive Test Circuit

Fig. 12b - Unclamped Inductive Waveforms

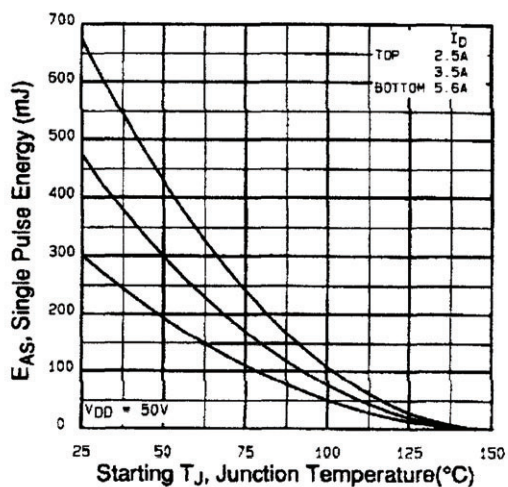


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

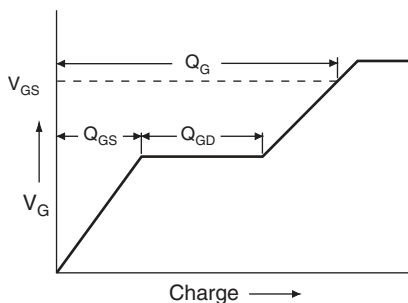


Fig. 13a - Basic Gate Charge Waveform

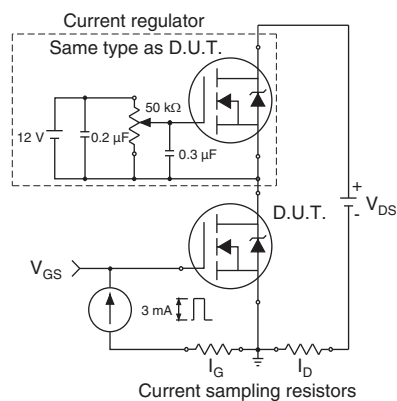
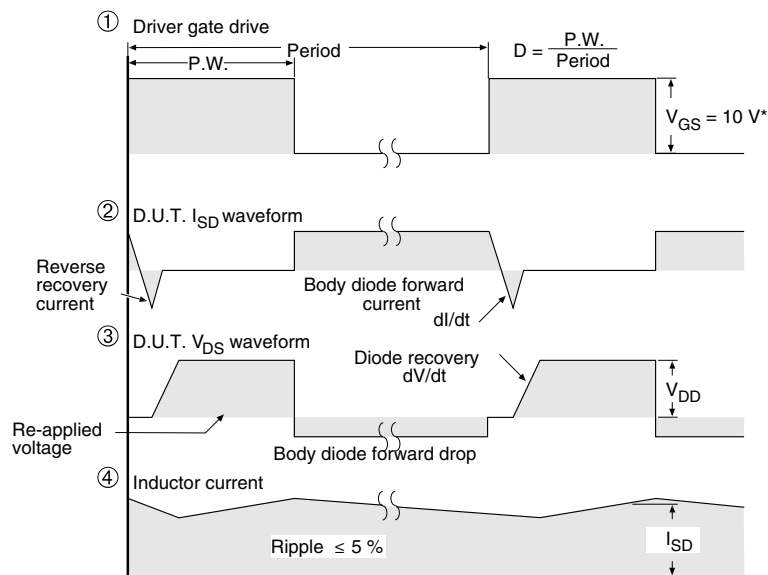
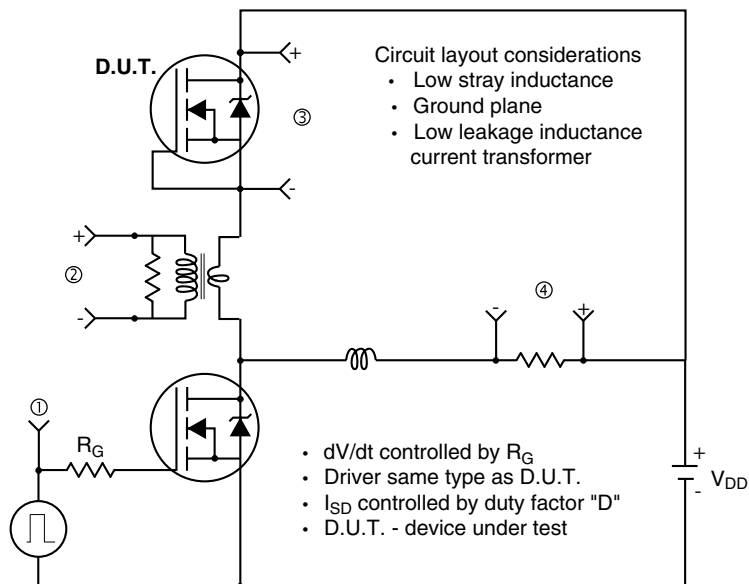


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



* $V_{GS} = 5 V$ for logic level devices and $3 V$ drive devices

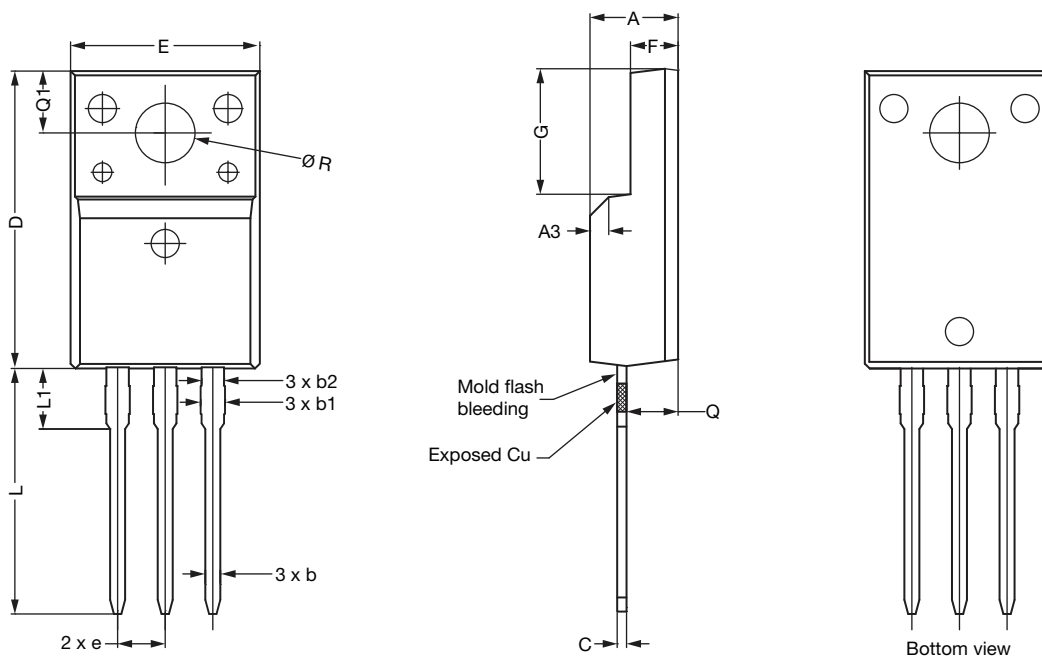
Fig. 14 - For N-Channel

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TO-220 FULLPAK (High Voltage)

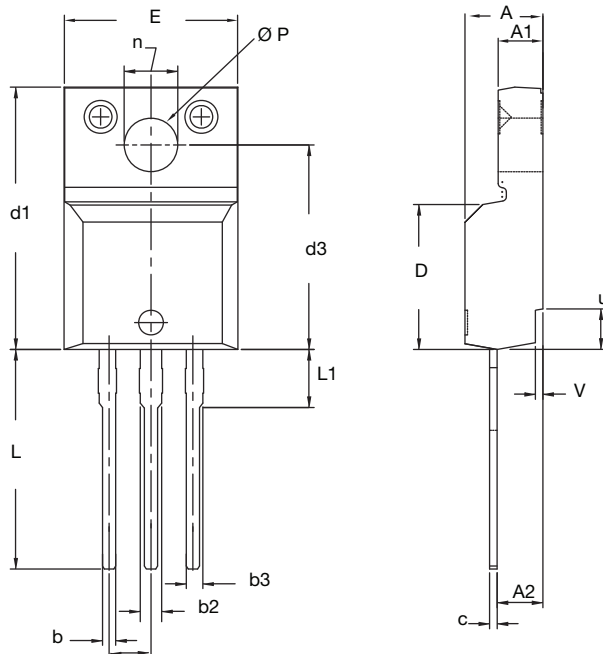
OPTION 1: FACILITY CODE = 9



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	4.60	4.70	4.80
b	0.70	0.80	0.91
b1	1.20	1.30	1.47
b2	1.10	1.20	1.30
C	0.45	0.50	0.63
D	15.80	15.87	15.97
e	2.54 BSC		
E	10.00	10.10	10.30
F	2.44	2.54	2.64
G	6.50	6.70	6.90
L	12.90	13.10	13.30
L1	3.13	3.23	3.33
Q	2.65	2.75	2.85
Q1	3.20	3.30	3.40
Ø R	3.08	3.18	3.28

Notes

1. To be used only for process drawing
2. These dimensions apply to all TO-220 FULLPAK leadframe versions 3 leads
3. All critical dimensions should C meet $C_{pk} > 1.33$
4. All dimensions include burrs and plating thickness
5. No chipping or package damage
6. Facility code will be the 1st character located at the 2nd row of the unit marking

**OPTION 2: FACILITY CODE = Y**

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.570	4.830	0.180	0.190
A1	2.570	2.830	0.101	0.111
A2	2.510	2.850	0.099	0.112
b	0.622	0.890	0.024	0.035
b2	1.229	1.400	0.048	0.055
b3	1.229	1.400	0.048	0.055
c	0.440	0.629	0.017	0.025
D	8.650	9.800	0.341	0.386
d1	15.88	16.120	0.622	0.635
d3	12.300	12.920	0.484	0.509
E	10.360	10.630	0.408	0.419
e	2.54 BSC		0.100 BSC	
L	13.200	13.730	0.520	0.541
L1	3.100	3.500	0.122	0.138
n	6.050	6.150	0.238	0.242
Ø P	3.050	3.450	0.120	0.136
u	2.400	2.500	0.094	0.098
V	0.400	0.500	0.016	0.020

ECN: E19-0180-Rev. D, 08-Apr-2019
DWG: 5972

Notes

1. To be used only for process drawing
2. These dimensions apply to all TO-220 FULLPAK leadframe versions 3 leads
3. All critical dimensions should C meet $C_{pk} > 1.33$
4. All dimensions include burrs and plating thickness
5. No chipping or package damage
6. Facility code will be the 1st character located at the 2nd row of the unit marking



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